Atsushi Nishikawa

List of Publications by Year
in descending order

45 papers	692 citations	759233 12 h-index	713466 21 g-index
45 all docs	45 docs citations	45 times ranked	441 citing authors

#	Article	IF	Citations
1	Room-Temperature Red Emission from a p-Type/Europium-Doped/n-Type Gallium Nitride Light-Emitting Diode under Current Injection. Applied Physics Express, 0, 2, 071004.	2.4	183
2	Eu luminescence center created by Mg codoping in Eu-doped GaN. Applied Physics Letters, 2012, 100, .	3.3	50
3	Site and sample dependent electronâ€"phonon coupling of Eu ions in epitaxial-grown GaN layers. Optical Materials, 2011, 33, 1050-1054.	3.6	48
4	Growth and characterization of InAsN alloy films and quantum wells. Journal of Crystal Growth, 2005, 278, 254-258.	1.5	33
5	Effect of nitrogen on the optical and transport properties of Ga0.48In0.52NyP1â^'y grown on GaAs(001) substrates. Applied Physics Letters, 2003, 83, 5446-5448.	3.3	32
6	High Critical Electric Field Exceeding 8 MV/cm Measured Using an AlGaNpâ€"iâ€"nVertical Conducting Diode onn-SiC Substrate. Japanese Journal of Applied Physics, 2007, 46, 2316-2319.	1.5	32
7	High critical electric field of AlxGa1â^'xN p-i-n vertical conducting diodes on n-SiC substrates. Applied Physics Letters, 2006, 88, 173508.	3.3	29
8	Lattice site location of optical centers in GaN:Eu light emitting diode material grown by organometallic vapor phase epitaxy. Applied Physics Letters, 2010, 97, 111911.	3.3	29
9	MBE growth and photoreflectance study of GaAsN alloy films grown on GaAs (001). Journal of Crystal Growth, 2003, 251, 427-431.	1.5	23
10	Room-temperature red emission from light-emitting diodes with Eu-doped GaN grown by organometallic vapor phase epitaxy. Optical Materials, 2011, 33, 1071-1074.	3.6	23
11	Electroluminescence properties of Eu-doped GaN-based red light-emitting diode by OMVPE. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1397-1399.	1.8	19
12	Electroluminescence Properties of Eu-doped GaN-based Light-emitting Diodes Grown by Organometallic Vapor Phase Epitaxy. Materials Research Society Symposia Proceedings, 2011, 1342, 27.	0.1	15
13	RF-MBE growth of InAsN layers on GaAs (001) substrates using a thick InAs buffer layer. Journal of Crystal Growth, 2003, 251, 422-426.	1.5	12
14	Effect of growth temperature on Eu-doped GaN layers grown by organometallic vapor phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2040-2042.	0.8	12
15	Current-voltage characteristics of pâ€•InGaNâ^•nâ€•GaN vertical conducting diodes on n+â€•SiC substrates. Applied Physics Letters, 2005, 87, 233505.	3.3	11
16	Growth and optical characterization of InAsN quantum dots. Physica Status Solidi (B): Basic Research, 2006, 243, 1657-1660.	1.5	11
17	Atmospheric pressure growth of Euâ€•doped GaN by organometallic vapor phase epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 445-448.	1.8	10
18	The effect of nitrogen on self-assembled GaInNAs quantum dots grown on GaAs. Physica Status Solidi (B): Basic Research, 2003, 240, 310-313.	1.5	9

#	Article	IF	Citations
19	Critical electric fields of AlGaN in AlGaN-based vertical conducting diodes on -SiC substrates. Superlattices and Microstructures, 2006, 40, 332-337.	3.1	9
20	Defect roles in the excitation of Eu ions in Eu:GaN. Optics Express, 2013, 21, 30633.	3.4	9
21	200-mm GaN-on-Si Based Blue Light-Emitting Diode Wafer with High Emission Uniformity. Japanese Journal of Applied Physics, 2013, 52, 08JB25.	1.5	9
22	In situ Eu doping into Al Ga1â^'N grown by organometallic vapor phase epitaxy to improve luminescence properties. Optical Materials, 2015, 41, 75-79.	3.6	8
23	Excitation power dependent photoluminescence of In0.7Ga0.3As1â^'xNx quantum dots grown on GaAs (001). Journal of Crystal Growth, 2005, 278, 244-248.	1.5	7
24	Temperature dependence of current-voltage characteristics of npn-type GaNâ^•InGaN double heterojunction bipolar transistors. Applied Physics Letters, 2007, 91, 133514.	3.3	7
25	Highly Uniform Electroluminescence from 150 and 200 mm GaN-on-Si-Based Blue Light-Emitting Diode Wafers. Applied Physics Express, 2013, 6, 095502.	2.4	7
26	Investigation of optical gain in Eu-doped GaN thin film grown by OMVPE method. Journal of Science: Advanced Materials and Devices, 2016, 1, 220-223.	3.1	7
27	Fluorescence XAFS Analysis of Eu-Doped GaN Layers Grown by Organometallic Vapor Phase Epitaxy. E-Journal of Surface Science and Nanotechnology, 2011, 9, 51-53.	0.4	6
28	Excellent uniformity on large diameter GaN on silicon LED wafer. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 624-627.	0.8	5
29	GaN-on-Si wafers for HEMTs with high power-driving capability. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 945-948.	0.8	5
30	High breakdown voltage with low on-state resistance of p-InGaNâ^•n-GaN vertical conducting diodes on n-GaN substrates. Applied Physics Letters, 2006, 89, 153509.	3.3	4
31	Low on-resistance of GaNp-i-n vertical conducting diodes grown on 4H-SiC substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2662-2665.	0.8	4
32	Nature and Excitation Mechanism of the Emission-dominating Minority Eu-center in GaN Grown by Organometallic Vapor-phase Epitaxy. Materials Research Society Symposia Proceedings, 2011, 1342, 67.	0.1	4
33	High breakdown field of pnp GaN/InGaN/AlGaN DHBTs with AlGaN collector. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 2037-2041.	1.8	3
34	Site Selective Magneto-Optical Studies of Eu ions in Gallium Nitride. Materials Research Society Symposia Proceedings, 2011, 1342, 93.	0.1	3
35	p-InGaN/n-GaN Vertical Conducting Diodes onn+-SiC Substrate for High Power Electronic Device Applications. Japanese Journal of Applied Physics, 2006, 45, 3387-3390.	1.5	2
36	Low-resistance graded AlxGa1â^'xN buffer layers for vertical conducting devices on n-SiC substrates. Journal of Crystal Growth, 2007, 298, 819-821.	1.5	2

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37	High-Temperature Characteristics of Al_xGa_{1-x}N-Based Vertical Conducting Diodes. Japanese Journal of Applied Physics, 2008, 47, 2838.	1.5	2
38	Low-temperature characteristics of the current gain of GaN/InGaN double-heterojunction bipolar transistors. Journal of Crystal Growth, 2009, 311, 3000-3002.	1.5	2
39	Development of new-type 1.5 Î¼m light-emitting devices based on Er,O-codoped GaAs. Journal of Physics: Conference Series, 2009, 165, 012025.	0.4	2
40	Improved Eu Luminescence Properties in Eu-Doped GaN Grown on GaN Substrates by Organometallic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2010, 49, 048001.	1.5	2
41	High-temperature (300 Â°C) operation ofnpn-type GaN/InGaN double heterojunction bipolar transistors. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2957-2959.	0.8	1
42	Dislocation generation in GaN by dicing process. Journal of Physics: Conference Series, 2013, 417, 012055.	0.4	1
43	Growth Temperature Dependence of Eu-Doped GaN Grown by Organometallic Vapor Phase Epitaxy. Zairyo/Journal of the Society of Materials Science, Japan, 2010, 59, 671-674.	0.2	0
44	Efficient luminescence from rare-earth elements by nitride-based nano-particle. Hosokawa Powder Technology Foundation ANNUAL REPORT, 2010, 18, 38-44.	0.0	0
45	Advanced Materials Design of Rare-Earth-Doped Semiconductors by Organometallic Vapor Phase Epitaxy. , 2013, , 261-272.		0